Accepted Manuscript

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PII: S0925-8388(18)33668-5

DOI: 10.1016/j.jallcom.2018.10.004

Reference: JALCOM 47822

To appear in: Journal of Alloys and Compounds

Received Date: 3 September 2018

Revised Date: 29 September 2018

Accepted Date: 1 October 2018

Please cite this article as: L. Li, W.B. Hong, G.Y. Chen, X.M. Chen, High-performance (1-x)(0.2B₂O₃– 0.8SiO₂)–xTiO₂ (x = 0.025–0.1) glass matrix composites for microwave substrate applications, *Journal of Alloys and Compounds* (2018), doi: https://doi.org/10.1016/j.jallcom.2018.10.004.

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High-performance $(1-x)(0.2B_2O_3-0.8SiO_2)-xTiO_2$ (x = 0.025-0.1) glass matrix composites for microwave substrate applications

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ABSTRACT

The (1-x)($0.2B_2O_3-0.8SiO_2$)-xTiO₂ (x = 0.025-0.1) glass matrix composites were prepared by a solid state sintering method, and high relative density >97% was obtained when the sintering temperature was 975-1000°C. The rutile and amorphous phases were indicated by XRD, and no crystallization of amorphous SiO₂ or chemical reaction was observed. With increasing x from 0 to 0.1, the dielectric constant (ε_r) increased slightly while the *Qf* value decreased, and the temperature coefficient of resonant frequency (τ_i) increased from a negative to a positive value. The optimized microwave dielectric properties were obtained as following: ε_r = 4.01, *Qf* = 66,800 GHz, τ_f = -2.2 ppm/°C for x =0.025 sintered at 1000°C, and ε_r = 4.22, *Qf* = 55,300 GHz, τ_f = 3.1 ppm/°C for x = 0.05 sintered at 975°C. The ultra-low ε_r , high *Qf* value and near-zero τ_f indicate that the present glass matrix composites are excellent candidates as the microwave substrate materials.

KEYWORDS: glass matrix composite; fused silica; microwave substrate

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